

BUK95/9606-40B

TrenchMOS™ logic level FET

Rev. 01 — 14 May 2003

Product data

1. Product profile

1.1 Description

N-channel enhancement mode field-effect power transistor in a plastic package using Philips High-Performance Automotive (HPA) TrenchMOS™ technology.

Product availability:

BUK9506-40B in SOT78 (TO-220AB)

BUK9606-40B in SOT404 (D²-PAK).

1.2 Features

- Very low on-state resistance
- 175 °C rated
- Q101 compliant
- Logic level compatible.

1.3 Applications

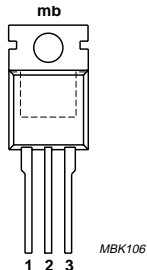
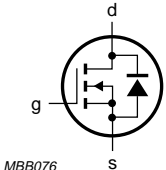
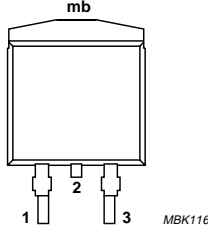
- Automotive systems
- Motors, lamps and solenoids
- 12 V loads
- General purpose power switching.

1.4 Quick reference data

- $E_{DS(AL)S} \leq 494$ mJ
- $I_D \leq 75$ A
- $R_{DSon} = 5.7$ m Ω (typ)
- $P_{tot} \leq 203$ W.

2. Pinning information

Table 1: Pinning - SOT78 and SOT404, simplified outlines and symbol

Pin	Description	Simplified outline	Symbol	
1	gate (g)	 MBK106	 MBB076	
2	drain (d) [1]			 MBK116
3	source (s)			
mb	mounting base, connected to drain (d)			

[1] It is not possible to make connection to pin 2 of the SOT404 package.



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3. Limiting values

Table 2: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)		-	40	V
V_{DGR}	drain-gate voltage (DC)	$R_{GS} = 20 \text{ k}\Omega$	-	40	V
V_{GS}	gate-source voltage (DC)		-	± 15	V
I_D	drain current (DC)	$T_{mb} = 25 \text{ }^\circ\text{C}$; $V_{GS} = 5 \text{ V}$; Figure 2 and 3	[1] -	129	A
			[2] -	75	A
		$T_{mb} = 100 \text{ }^\circ\text{C}$; $V_{GS} = 5 \text{ V}$; Figure 2	[2] -	75	A
I_{DM}	peak drain current	$T_{mb} = 25 \text{ }^\circ\text{C}$; pulsed; $t_p \leq 10 \text{ }\mu\text{s}$; Figure 3	-	516	A
P_{tot}	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$; Figure 1	-	203	W
T_{stg}	storage temperature		-55	+175	$^\circ\text{C}$
T_j	junction temperature		-55	+175	$^\circ\text{C}$
Source-drain diode					
I_{DR}	reverse drain current (DC)	$T_{mb} = 25 \text{ }^\circ\text{C}$	[1] -	129	A
			[2] -	75	A
I_{DRM}	peak reverse drain current	$T_{mb} = 25 \text{ }^\circ\text{C}$; pulsed; $t_p \leq 10 \text{ }\mu\text{s}$	-	516	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; $I_D = 75 \text{ A}$; $V_{DS} \leq 40 \text{ V}$; $V_{GS} = 5 \text{ V}$; $R_{GS} = 50 \text{ }\Omega$; starting $T_{mb} = 25 \text{ }^\circ\text{C}$	-	494	mJ

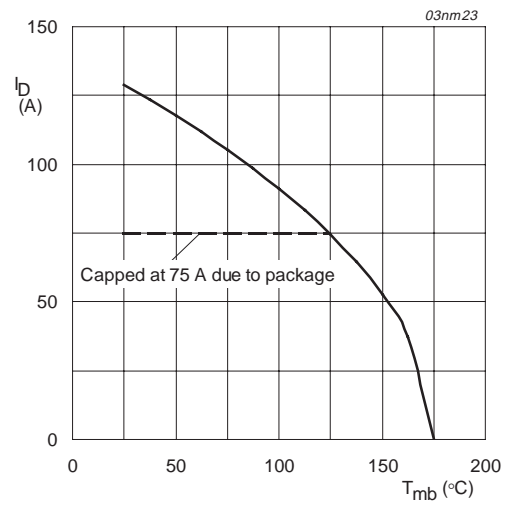
[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.



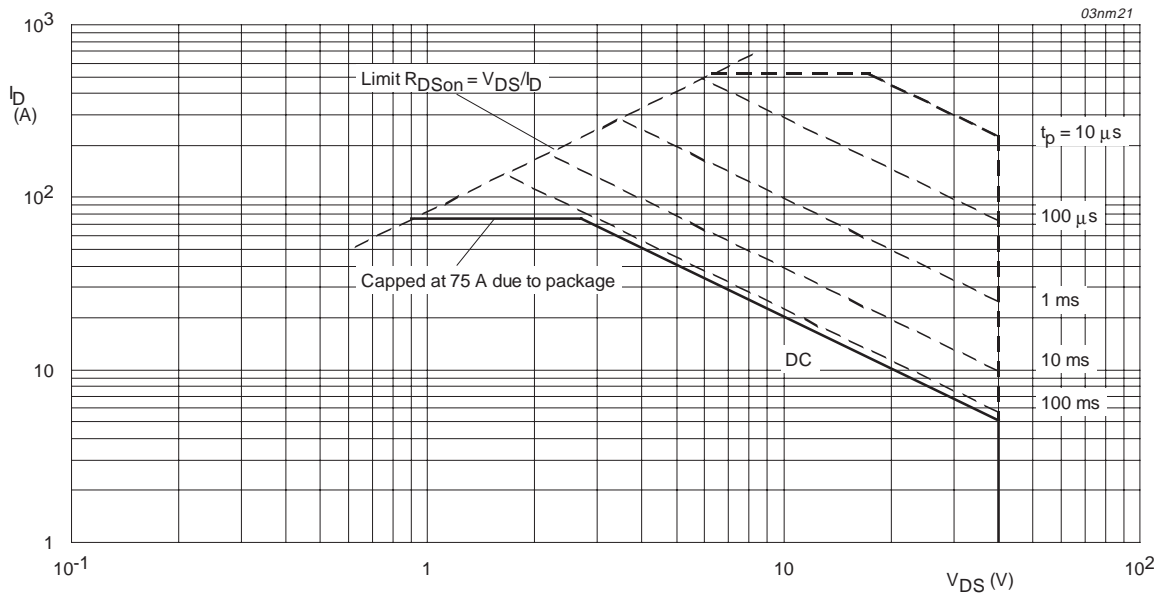
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature.



$V_{GS} \geq 5 V$

Fig 2. Continuous drain current as a function of mounting base temperature.



$T_{mb} = 25^{\circ}C$; I_{DM} single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

4. Thermal characteristics

Table 3: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	-	-	0.74	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient					
	SOT78 (TO-220AB)	vertical in still air	-	60	-	K/W
	SOT404 (D ² -PAK)	minimum footprint; mounted on a PCB	-	50	-	K/W

4.1 Transient thermal impedance

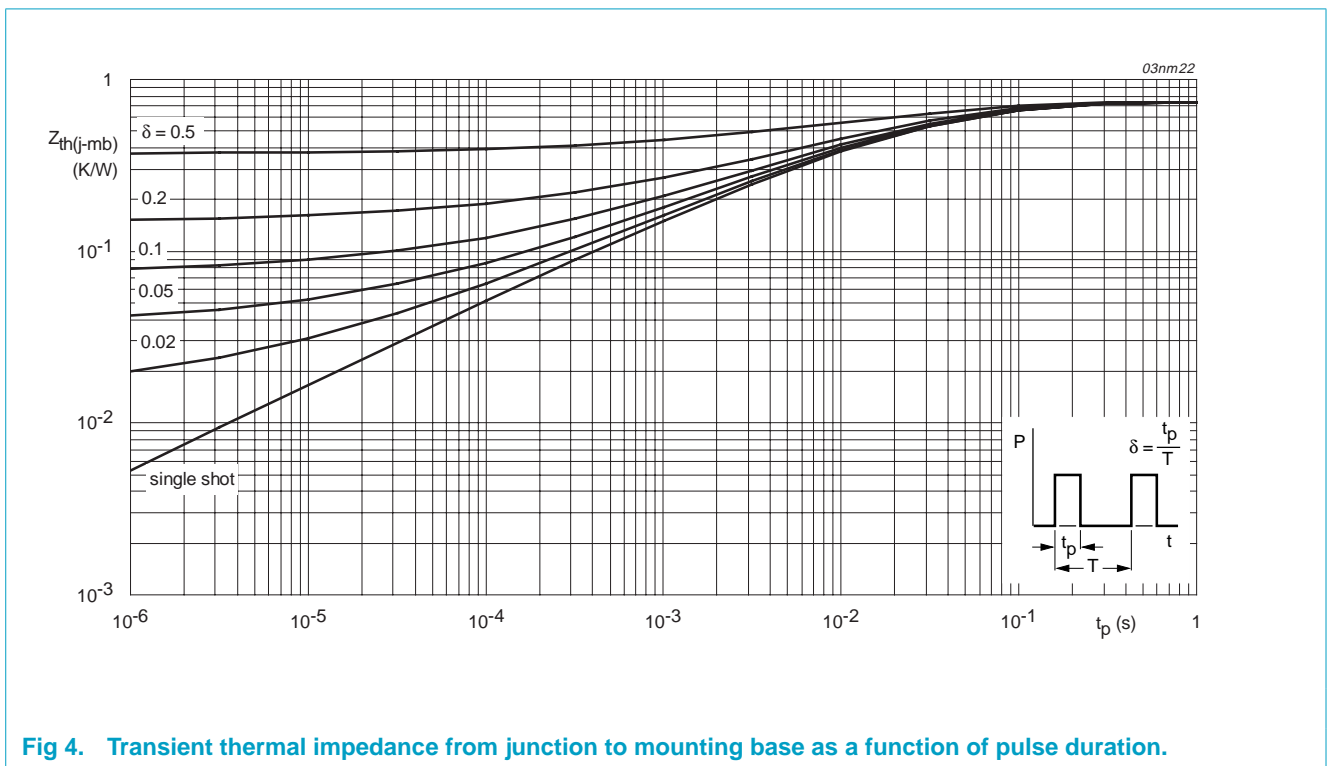


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration.

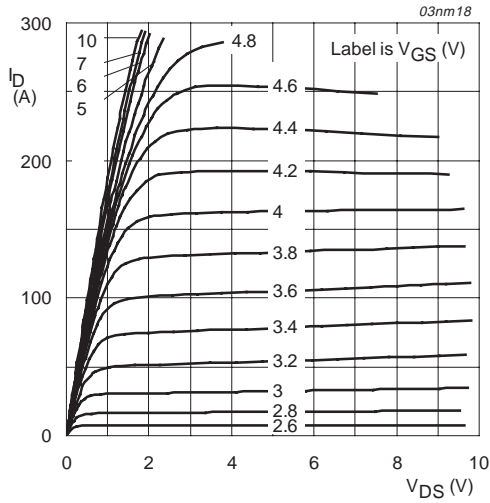
5. Characteristics

Table 4: Characteristics
 $T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25\text{ mA}; V_{GS} = 0\text{ V}$				
		$T_j = 25\text{ °C}$	40	-	-	V
		$T_j = -55\text{ °C}$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}; V_{DS} = V_{GS};$ Figure 9				
		$T_j = 25\text{ °C}$	1.1	1.5	2	V
		$T_j = 175\text{ °C}$	0.5	-	-	V
		$T_j = -55\text{ °C}$	-	-	2.3	V
I_{DSS}	drain-source leakage current	$V_{DS} = 40\text{ V}; V_{GS} = 0\text{ V}$				
		$T_j = 25\text{ °C}$	-	0.02	1	μA
		$T_j = 175\text{ °C}$	-	-	500	μA
I_{GSS}	gate-source leakage current	$V_{GS} = \pm 15\text{ V}; V_{DS} = 0\text{ V}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 5\text{ V}; I_D = 25\text{ A};$ Figure 7 and 8				
		$T_j = 25\text{ °C}$	-	5.7	6.4	m Ω
		$T_j = 175\text{ °C}$	-	-	12.2	m Ω
		$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A}$	-	-	7.1	m Ω
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A}$	-	4.1	5	m Ω
Dynamic characteristics						
$Q_{g(tot)}$	total gate charge	$V_{GS} = 5\text{ V}; V_{DD} = 32\text{ V};$ $I_D = 25\text{ A};$ Figure 14	-	44	-	nC
Q_{gs}	gate-source charge		-	11	-	nC
Q_{gd}	gate-drain (Miller) charge		-	17	-	nC
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V};$ $f = 1\text{ MHz};$ Figure 12	-	3967	4901	pF
C_{oss}	output capacitance		-	634	760	pF
C_{rss}	reverse transfer capacitance		-	278	380	pF
$t_{d(on)}$	turn-on delay time	$V_{DD} = 30\text{ V}; R_L = 1.2\text{ }\Omega;$ $V_{GS} = 5\text{ V}; R_G = 10\text{ }\Omega$	-	43	-	ns
t_r	rise time		-	145	-	ns
$t_{d(off)}$	turn-off delay time		-	132	-	ns
t_f	fall time		-	92	-	ns
L_d	internal drain inductance	from drain lead 6 mm from package to center of die	-	4.5	-	nH
		from contact screw on mounting base to center of die SOT78	-	3.5	-	nH
		from upper edge of drain mounting base to center of die SOT404	-	2.5	-	nH
L_s	internal source inductance	from source lead to source bond pad	-	7.5	-	nH

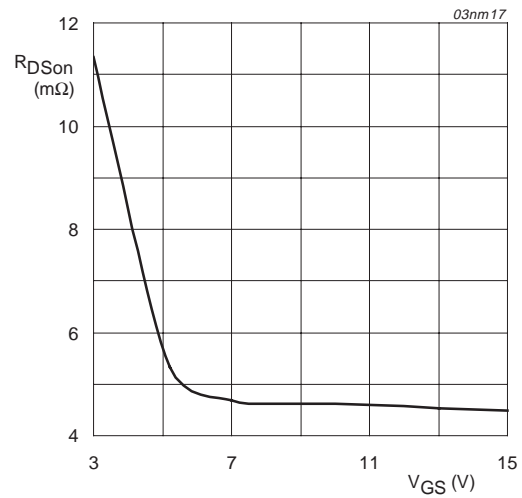
Table 4: Characteristics...continued*T_j = 25 °C unless otherwise specified.*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V _{SD}	source-drain (diode forward) voltage	I _S = 25 A; V _{GS} = 0 V; Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs	-	61	-	ns
Q _r	recovered charge	V _{GS} = -10 V; V _{DS} = 30 V	-	57	-	nC



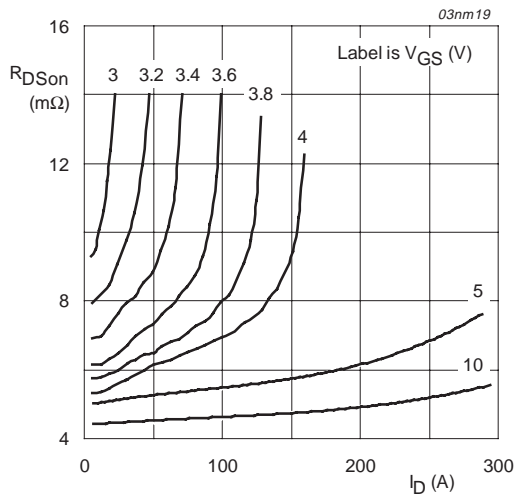
$T_j = 25\text{ }^\circ\text{C}$; $t_p = 300\text{ }\mu\text{s}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



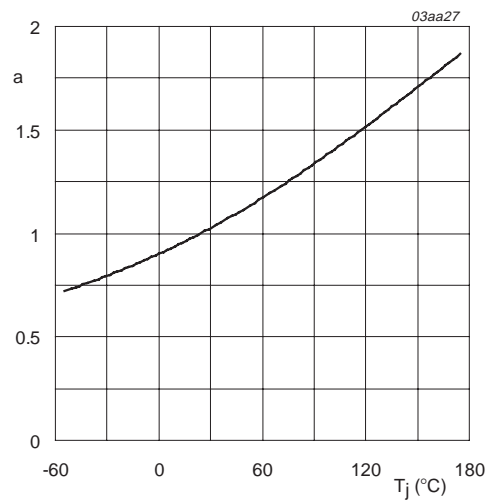
$T_j = 25\text{ }^\circ\text{C}$; $I_D = 25\text{ A}$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values.



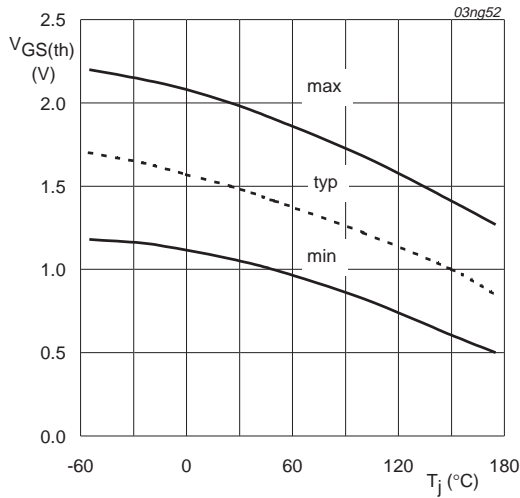
$T_j = 25\text{ }^\circ\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



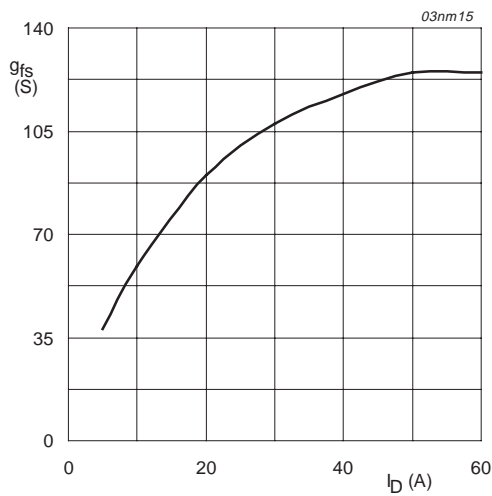
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



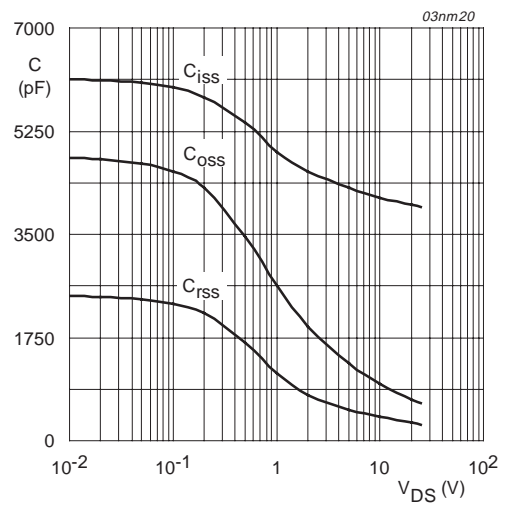
$T_J = 25 \text{ }^\circ\text{C}; V_{DS} = V_{GS}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



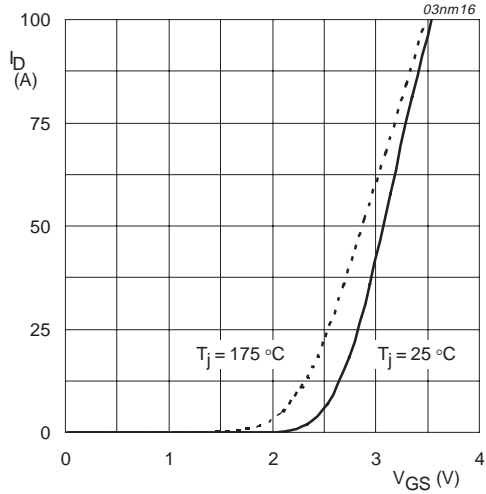
$T_J = 25 \text{ }^\circ\text{C}; V_{DS} = 25 \text{ V}$

Fig 11. Forward transconductance as a function of drain current; typical values.



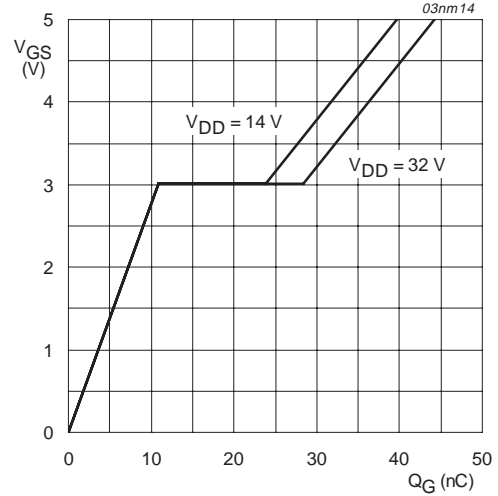
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



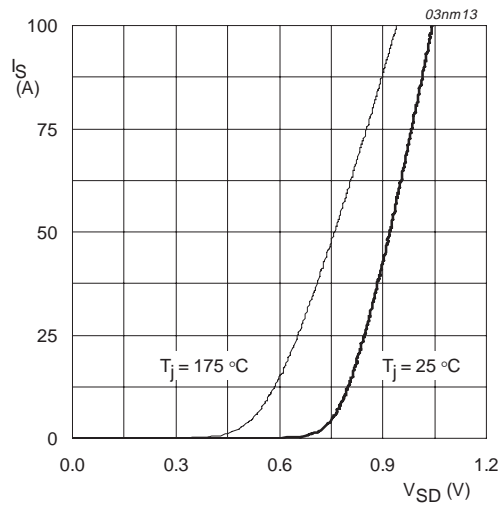
$V_{DS} = 25\text{ V}$

Fig 13. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



$T_j = 25\text{ °C}; I_D = 25\text{ A}$

Fig 14. Gate-source voltage as a function of gate charge; typical values.



$V_{GS} = 0\text{ V}$

Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.

6. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



Fig 16. SOT78 (TO-220AB).

Plastic single-ended surface mounted package (Philips version of D²-PAK); 3 leads
(one lead cropped)

SOT404

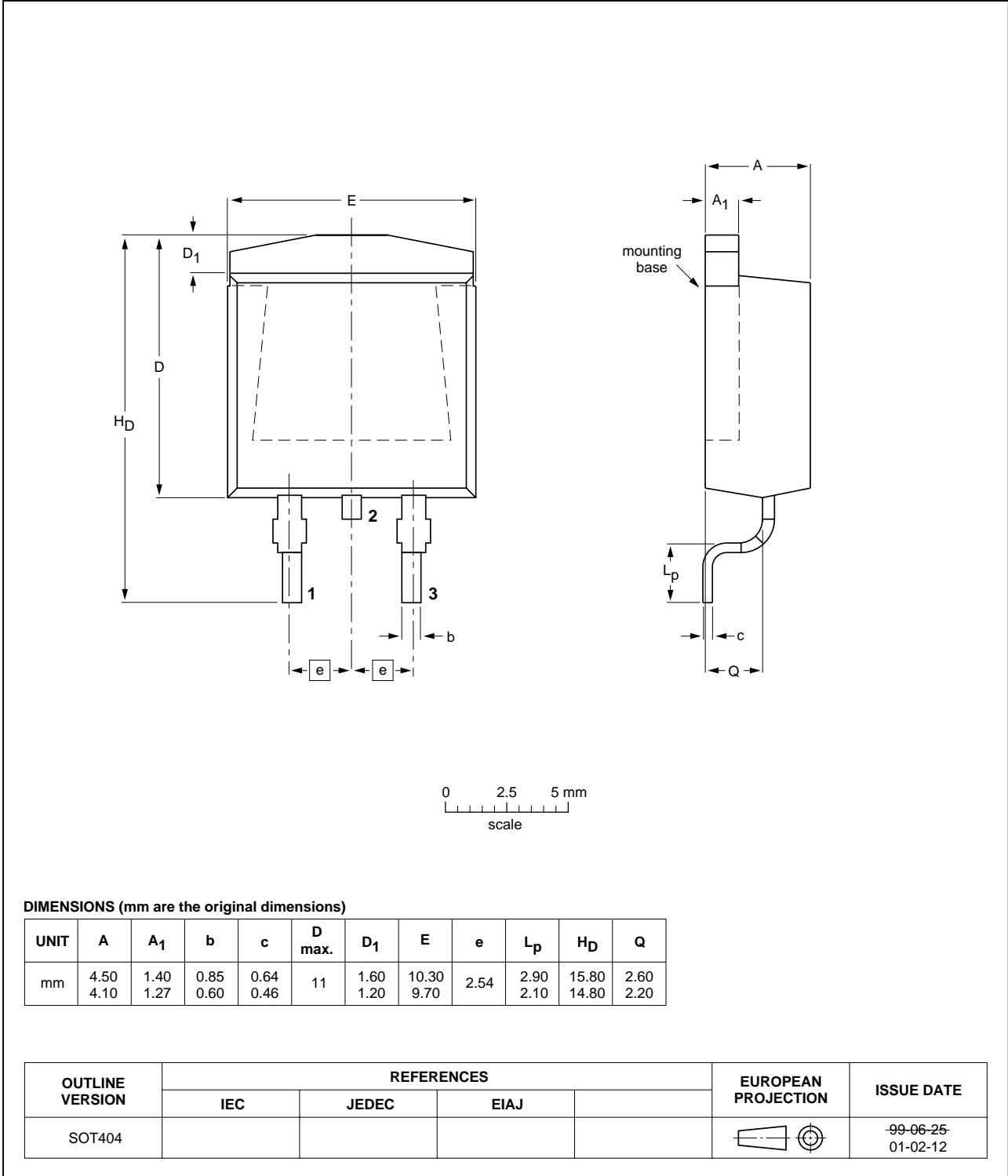
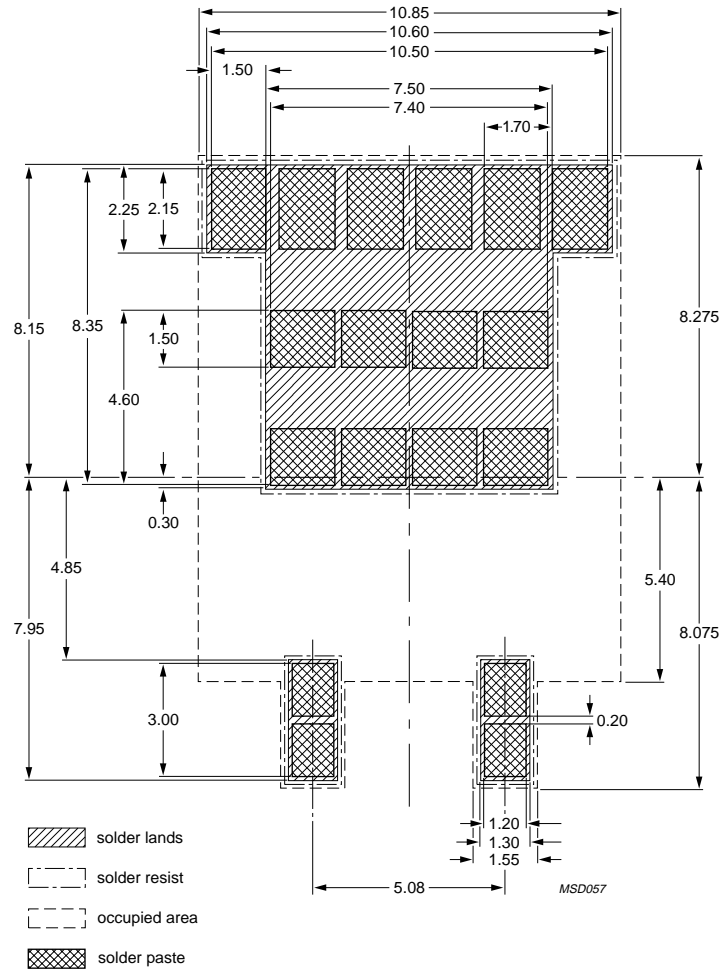


Fig 17. SOT404 (D²-PAK).

7. Soldering



Dimensions in mm.

Fig 18. Reflow soldering footprint for SOT404.

8. Revision history

Table 5: Revision history

Rev	Date	CPCN	Description
01	20030514	-	Product data (9397 750 11241)

9. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2][3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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